

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MSC80914** is Designed for Class C, Common Base General Purpose Applications to 2.3 GHz.

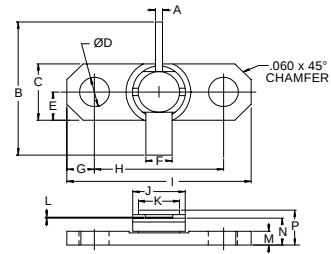
FEATURES INCLUDE:

- Gold Metalization
- Site Emitter Ballasting

MAXIMUM RATINGS

I_C	200 mA
V_{CC}	35 V
P_{DISS}	7.0 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	20 °C/W

PACKAGE STYLE .250 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1.0 mA	45			V
BV_{CER}	I _C = 5.0 mA R _{BE} = 10 Ω	45			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CBO}	V _{CB} = 28 V			0.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	15		150	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz		3.0	3.5	pF
P_{out}	V _{CC} = 28 V P _{in} = 200 mW fo = 2.0 GHz	1.0	1.25		W
P_G		7.0	8.0		dB
η_c		35	40		%